

Notice of References CitedApplication/Control No.
08/903,453Applicant(s)/Patent Under Reexam
Forbes et al.Examiner
George C. Eckert IIArt Unit
2815

Page 1 of 1

U.S. PATENT DOCUMENTS

	Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Name	Classification ²
A				
B				
C				
D				
E				
F				
G				
H				
I				
J				
K				
L				
M				

FOREIGN PATENT DOCUMENTS

	Document Number Country Code-Number-Kind Code	Date MM-YYYY ¹	Country	Name	Classification ²
N					
O					
P					
Q					
R					
S					
T					

NON-PATENT DOCUMENTS

	Include, as applicable: Author, Title, Date, Publisher, Edition or Volume, Pertinent Pages
U	Capasso et al., New Floating-Gate AlGaAs/GaAs Memory Devices with Graded-Gap Electron Injector and Long Retention Times, August 1988, IEEE, Electron Device Letters, Vol. 9, No. 8, pp. 377-79.
V	Burns et al., Principles of Electronic Circuits, 1987, West Publishing, p. 380.
W	Ng, Complete Guide to Semiconductor Devices, 1995, McGraw Hill, pp. 322-28, 605-08.
X	Wolf, Silicon Processing for the VLSI Era, Volume 2: Process Integration, 1990, Lattice Press, pp. 623-28.

^{*} A copy of this reference is not being furnished with this Office action. See MPEP § 707.05(a).¹ Dates in MM-YYYY format are publication dates.² Classifications may be U.S. or foreign.